

Active

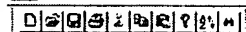
- L1: (3796) (opening trench via hole recess) with ((plasma gas) near (h2 hydrogen))
- L2: (78) 1 and (opening trench via hole recess) with ((plasma gas) near (chlorine))
- L6: (2) 5 and (opening trench via hole recess) with (silicide)
- L5: (18) 2 and (opening trench via hole recess) with (insulat\$3 dielectric)

Failed

2 and (opening trench via hole recess) with (insulat\$3 dielectric)

ERS form ISAR form Image Text HTML

	U	Document I	Issue Dat	Page	Title	Current O	Current X	Retrieval	Inventor	S	C	P	2	3	4	5
1		US 2005003757.7	2005021		Method of fabricating semiconductor device	438/270			Numazawa, Sumito et al.							
2		US 2004016665.6	2004082		METHOD OF FABRICATING SEMIC	438/589	257/E21.4		Numazawa, Sumito et al.							
3		US 2003012480.3	2003070		Method of fabricating semiconductor device	438/270	257/E21.4		Numazawa, Sumito et al.							
4		US 2003001331.6	2003011	23	Process for fabricating semiconductor device	438/706	257/E21.2		Negishi, Nobuyuki et al.							
5		US 2002009865.5	2002072		Method of fabricating semiconductor device	438/270	257/E21.4		Numazawa, Sumito et al.							
6		US 2002000986.4	2002012		Method of fabricating semiconductor device	438/589	257/288;		Numazawa, Sumito et al.							
7		US 6803281 B2	2004101		Method of fabricating semiconductor device	438/270	257/288;		Numazawa, Sumito et al.							
8		US 6720220 B2	2004041		Method of fabricating semiconductor device	438/270	257/288;		Numazawa, Sumito et al.							
9		US 6645870 B2	2003111	21	Process for fabricating semiconductor device	438/710	257/E21.2		Negishi, Nobuyuki et al.							
10		US 6512265 B2	2003012		Method of fabricating semiconductor device	257/330	257/288;		Numazawa, Sumito et al.							
11		US 6410959 B2	2002062		Method of fabricating semiconductor device	257/330	257/341;		Numazawa, Sumito et al.							
12		US 6307231 B1	2001102		Method of fabricating semiconductor device	257/330	257/341;		Numazawa, Sumito et al.							



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Failed

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DB: US-PG-PUB; USPAT; EP; JPO ☐ Details ☐ Highlight all hits initially

Default operator: [OR]

2 and (opening trench via hole recess) with (insulat\$3 dielectric)

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	U	Document I	Issue Dat	Page	Title	Current O	Current X	Retrieval	Inventor	S	C	P	2	3	4	5	6	7	8	9	0
7		US 6803281	2004101		Method of fabricating semiconductor device	438/270	257/288;		Numazawa; Sumito et al.												
8		B2	2		Method of fabricating semiconductor device	438/270	257/328;		Numazawa; Sumito et al.												
9		US 6720220	2004041		Method of fabricating semiconductor device		257/288;		Numazawa; Sumito et al.												
10		B2	3		Process for fabricating semiconductor device	438/710	257/328;		Negishi; Nobuyuki et al.												
11		US 6645870	2003111	21	Method of fabricating semiconductor device		257/E21.2		Numazawa; Sumito et al.												
12		B2	1		Method of fabricating semiconductor device	257/330	257/288;		Numazawa; Sumito et al.												
13		US 6512265	2003012		Method of fabricating semiconductor device	257/330	257/328;		Numazawa; Sumito et al.												
14		B2	8		Method of fabricating semiconductor device	257/330	257/341;		Numazawa; Sumito et al.												
15		US 6410959	2002062		Method of fabricating semiconductor device		257/342;		Numazawa; Sumito et al.												
16		US 6307231	2001102		Method of fabricating semiconductor device	257/330	257/341;		Numazawa; Sumito et al.												
17		B1	3		Method of fabricating semiconductor device	438/270	257/342;		Numazawa; Sumito et al.												
18		US 6168996	2001010		Method of fabricating semiconductor device		257/330;		Numazawa; Sumito et al.												
19		B1	2		Integrated procedure for high yield production of	422/234	257/E21.4		Dawkins; John L.												
20		US 5458858	1995101		Integrated procedure for high yield production of	423/478	422/200;		Westerlund; G. Oscar												
21		A	7		Semiconductor integrated circuit	257/520	204/277;		Taguchi; Minoru												
22		US 5324497	1994062				204/278;		ODA, KATSUYA												
23		A	8				257/378;		SHIOTANI, YOSHIMI et al.												
24		US 4935800	1990061				257/501;														
25		A	9																		
26		JP	2001051		METHOD OF FORMING SEMICONDUCTOR DE																
27		2001126989	1		MANUFACTURE OF SEMICONDUCTOR DE																
28		JP	1992101				438/701;														
29		04286115.A	2				438/714;														

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